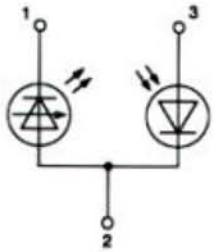
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RLT6405G TECHNICAL DATA

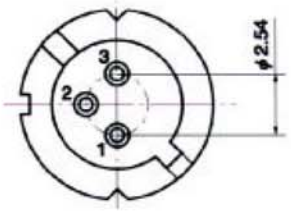
Short Wavelength Laserdiode

Structure: **AlGaInP, index guided**
Lasing wavelength: **640 nm**
Max. optical power: **5 mW**
Package: **9 mm**

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	5	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	T_C	-10 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free			5	mW
Threshold Current	I_{th}		35	45	55	mA
Operation Current	I_{op}	P_o =5mW	45	55	70	mA
Operating Voltage	V_{op}	P_o =5mW	2.0	2.4		V
Lasing Wavelength	λ_p	P_o =5mW		640	645	nm
Beam Divergence	$\theta_{=}$	P_o =5mW	8	10	11	°
Beam Divergence	$\theta_{\perp}$	P_o =5mW	25	31	40	°
Monitor Current	I_m	P_o =5mW, V_r=5V	5	10	20	µA
Slope Efficiency	η	mW/mA	0.1	0.3	0.5	
Astigmatism	A_s	P_o =5mW		11		µm